TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

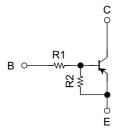
## RN2707JE, RN2708JE, RN2709JE

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications.

Unit in mm

- Two devices are incorporated into an Extreme-Super-Mini (5 pin) package.
- Incorporating a bias resistor into a transistor reduces parts count.
   Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Wide range of resistor values are available to use in various circuit designs.
- Complementary to RN1707JE~1709JE

#### **Equivalent Circuit and Bias Resistor Values**



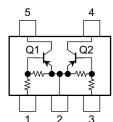
Type No.	R1 (kΩ)	R2 (kΩ)
RN2707JE	10	47
RN2708JE	22	47
RN2709JE	47	22

1.6±0.05 1.2±0.05	
1.0±0.05 0.5 0.5 0.5 0.5 1.0±0.05 1.6±0.05	
0.12±0.05	
1. BASE 1 (B1) 2. EMITTER (E) 3. BASE 2 (B2) 4. COLLECTOR 2 (C2)	
ESV 5. COLLECTOR 1 (C1)	
JEDEC —	
EIAJ —	
TOSHIBA —	

### Maximum Ratings (Ta = 25°C) (Q1, Q2 common)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage	RN1707JE~1709JE	$V_{CBO}$	-50	٧	
Collector-emitter voltage	1111110102 110002	$V_{CEO}$	-50	٧	
	RN1707JE		-6	V	
Emitter-base voltage	RN1708JE	$V_{EBO}$	-7		
	RN1709JE		-15		
Collector current		Ic	-100	mA	
Collector power dissipation	RN1707JE~1709JE	P <sub>C</sub> (Note)	100	mW	
Junction temperature	KN17073E~17093E	Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	<b>−55~150</b>	°C	

# Equivalent Circuit (top view)



Note: Total rating

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### Electrical Characteristics (Ta = 25°C) (Q1, Q2 common)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	RN2707JE~2709JE	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-100	nA
	KN2/0/JE~2/09JE	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_B = 0$	_	_	-500	
	RN2707JE		$V_{EB} = -6 \text{ V}, I_C = 0$	-0.081	_	-0.15	
Emitter cut-off current	RN2708JE	I <sub>EBO</sub>	$V_{EB} = -7 \text{ V}, I_{C} = 0$	-0.078	_	-0.145	mA
	RN2709JE		$V_{EB} = -15 \text{ V}, I_C = 0$	-0.167	_	-0.311	
	RN2707JE			80	_	_	
DC current gain	RN2708JE	h <sub>FE</sub>	$V_{CE} = -5 \text{ V},$ $I_{C} = -10 \text{ mA}$	80	_	_	
	RN2709JE	=		70	_	_	
Collector-emitter saturation voltage	RN2707JE~2709JE	V <sub>CE (sat)</sub>	$I_C = -5 \text{ mA},$ $I_B = -0.25 \text{ mA}$	_	-0.1	-0.3	٧
Input voltage (ON)	RN2707JE	V <sub>I (ON)</sub>		-0.7	_	-1.8	V
	RN2708JE		$V_{CE} = -0.2 \text{ V},$ $I_{C} = -5 \text{ mA}$	-1.0	_	-2.6	
	RN2709JE			-2.2	_	-5.8	
	RN2707JE	V <sub>I</sub> (OFF)	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -0.1 mA	-0.5	_	-1.0	V
Input voltage (OFF)	RN2708JE			-0.6	_	-1.16	
	RN2709JE			-1.5	_	-2.6	
Transition frequency	RN2707JE~2709JE	f <sub>T</sub>	$V_{CE} = -10 \text{ V},$ $I_{C} = -5 \text{ mA}$	_	200	_	MHz
Collector output capacitance	RN2707JE~2710JE	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_{E} = 0,$ f = 1 MHz	_	3	6	pF
	RN2707JE	R1	_	7	10	13	
Input resistor	RN2708JE			15.4	22	28.6	kΩ
	RN2709JE			32.9	47	61.1	
Resistor ratio	RN2707JE	R1/R2	_	0.191	0.213	0.232	
	RN2708JE			0.421	0.468	0.515	
	RN2709JE			1.92	2.14	2.35	

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The information contained herein is subject to change without notice.

Type Name	Marking
RN2707JE	Type name
RN2708JE	Type name
RN2709JE	Type name